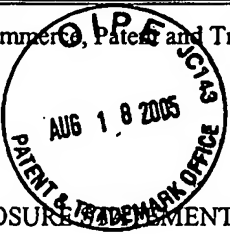
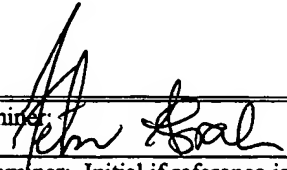
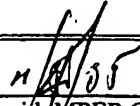
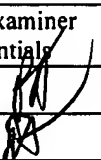
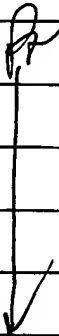


U.S. Department of Commerce, Patent and Trademark Office  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Application No.:	10/771,593
	Filing Date:	02/02/2004
	First Named Inventor:	Hamza Yilmaz
	Group Art Unit:	2826
	Examiner Name:	Fetsum Abraham
	Confirmation No.:	3820
	Attorney Docket No.:	YMZ004 US

U.S. Patent Documents							
*Examiner Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
P	1.	2004/0084721 A1	05/06/2004	Kocon et al.	257	328	11/05/2002
Foreign Patent Documents							
							Translation
		Document	Date	Country	Class	Subclass	Yes No
✓	2.	EP 1073110 A1	01/31/2001	Europe	21	329	X
	3.	EP 1369927 A2	12/10/2003	Europe	29	78	
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Examiner: 	Date Considered: 
* Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication with applicant.	

U.S. Patent Documents								
*Examiner Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
	1.	5,168,331	12/01/92	Yilmaz	257	331		
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Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
Other Art (Including Author, Title, Date, Pertinent Pages, Etc.)								
	3.	Jongdae Kim et al., "High-Density Trench DMOSFETs Employing Two Step Trench Technique and Trench Contact Structure", ISPSD-2003 Proceedings, pp. 1-4						
	4.	Il-Yong Park et al., "Novel Process Techniques for Fabricating High Density Trench MOSFETs with Self-Aligned N ⁺ /P ⁺ Source Formed on the Trench Side Wall", ISPSD-2003 Proceedings, pp. 1-4.						
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	7.	Syotaro Ono et al., "30V New Fine Trench MOSFET with Ultra Low On-Resistance", ISPSD-2003 Proceedings, pp. 1-4.						

Examiner: <i>John H. Neal</i>	Date Considered: <i>11/24/05</i>
<p>* Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication with applicant.</p>	